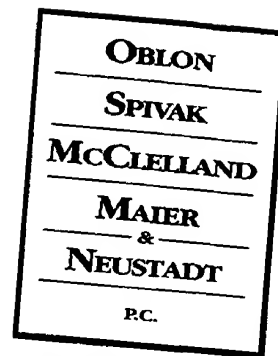




Docket No.: 206169US99

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313



RE: Application Serial No.: 09/766,046  
Applicants: Jamal RAMDANI, et al.

Filing Date: January 19, 2001

For: STRUCTURE AND METHOD FOR FABRICATING  
GAN DEVICES UTILIZING THE FORMATION OF A  
COMPLIANT SUBSTRATE

Group Art Unit: 2815

Examiner: BAUMEISTER

SIR:

Attached hereto for filing are the following papers:

**SUPPLEMENTAL AMENDMENT W/MARKED-UP COPY**

Our check in the amount of \$0.00 is attached covering any required fees. In the event any variance exists between the amount enclosed and the Patent Office charges for filing the above-noted documents, including any fees required under 37 C.F.R. 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, please charge or credit the difference to our Deposit Account No. 15-0030. Further, if these papers are not considered timely filed, then a petition is hereby made under 37 C.F.R. 1.136 for the necessary extension of time. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.

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John H

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

JAMAL RAMDANI ET AL

SERIAL NO: 09/766,046

FILED: JANUARY 19, 2001

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SUPPLEMENTAL AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Responsive to the Office Communication dated May 12, 2003, please amend the  
above-identified application as follows.

IN THE CLAIMS

Please amend Claim 9 as follows.

--9. (Amended) The semiconductor structure of Claim 8, wherein the Zintl-type  
phase material comprises at least one of  $\text{SrAl}_2$ ,  $\text{SrAl}_4$ ,  $(\text{MgCaYb})\text{Ga}_2$ ,  $(\text{Ca}, \text{Sr}, \text{Eu}, \text{Yb})\text{In}_2$ ,  
 $\text{BaGe}_2\text{As}$ , and  $\text{SrSn}_2\text{As}_2$ .--

SUPPORT FOR AMENDMENT

Applicants appreciate the close review of their response filed March 3, 2003, and

C'